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Effect of titanium carbide addition on the thermoelectric properties of B_4C ceramics

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Abstract

TiB₂/B₄C composite ceramics are prepared via hot pressing, in which the TiB₂ particles are formed by introducing TiC_{0.78} and through the reaction between B₄C and TiC_{0.78}. The electrical and thermal conductivities and Seebeck coefficient of samples containing 0, 12.5 and 25.4 vol% TiB₂ are measured from room temperature up to 1200 K. The results show that the transport properties of the samples vary with the TiB₂ content. The transport properties of a 12.5 vol% TiB₂/B₄C sample are dominated by the B₄C matrix as in undoped B₄C ceramics, whilst the transport properties of a 25.4 vol% TiB₂/B₄C sample are dominated by TiB₂ particles. The figure of merit of the 25.4 vol% TiB₂/B₄C sample is higher than that of the undoped B₄C ceramic sample between room temperature and about 700 K, which indicates that it is possible to improve the thermoelectric properties by selecting an optimum combination of different materials. © 2000 Elsevier Science Ltd. All rights reserved.

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1. Introduction

Recently, there has been renewed interest in thermoelectric materials [1,2]. The efficiency of a thermoelectric material depends on its material properties through the dimensionless figure of merit ZT ($ZT = \sigma \alpha^2 T/\kappa$, where σ , α , κ , and T are the electrical conductivity, Seebeck coefficient, thermal conductivity and temperature, respectively). For both applications in refrigeration and power generation, the efficiency increases monotonically with ZT [3]. So far the highest ZT value of the thermoelectric materials has been about 1, which leads to rather low efficiencies. Hence, until now thermoelectric materials have been only used in applications where reliability or convenience is more important than economy. In order to increase the value of ZT, many approaches, such as novel alloys [4] and low-dimensional structures [5], have been developed.

Much progress has been made [1,2]. But none of these approaches have yet made a breakthrough.

In the present work, an approach using composite thermoelectric materials, namely B₄C-based composites, is investigated experimentally. According to an effective-medium theory (EMT) [6], the ZT of a matrix-based particulate composite is always less than that the biggest ZT of each component of the composite, which implies that there can be no improvement in ZT for such particulate composites. However, the EMT prediction may be invalid for the nonmatrix-based composites, such as those with percolation cluster structures. In these systems, if one phase has much higher electrical conductivity than the matrix, the electrical conductivity of the composite can change by several orders of magnitude for a very small change in the volume fraction of the high conducting phase near its percolation threshold (ϕ_c) [7,8]. Therefore, if the Seebeck coefficient and thermal conductivity for the composite do not change rapidly near $\phi_{\rm c}$, it is possible to get a higher value of ZT for the composite than that for the matrix.

Boron-rich carbides (e.g. B_{6.5}C) are considered as

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Fig. 1. Electrical conductivity of the samples as a function of temperature.

potential materials for very high temperature thermoelectric energy conversion [9]. Compared with boron-rich carbides, B_4C has a lower electrical conductivity, a little higher thermal conductivity and almost the same Seebeck coefficient, and thus its ZT is lower than that of the boron-rich carbides. If the electrical conductivity of B_4C could be increased significantly, while its Seebeck coefficient and thermal conductivity do not change very much, B_4C would exhibit a larger ZT value [10]. In this paper, we select B_4C as the thermoelectric (semiconductor) phase and more highly conducting (metallic) TiB₂ as the second phase. TiB₂ is introduced into the B_4C by adding TiC_{0.78} and then through the reaction between TiC_{0.78} and B_4C [11]:

$$\mathrm{TiC}_{0.78} + \mathrm{B}_{4}\mathrm{C} \to \mathrm{TiB}_{2} + \mathrm{C},\tag{1}$$

which occurs at the high temperature, at which the composite was sintered.



Fig. 2. Seebeck coefficient of the samples as a function of temperature.



Fig. 3. Thermal conductivity of the samples as a function of temperature.

2. Experimental

 B_4C powder (average particle size 0.5 μ m, Moudanjiang boron carbide powder plant, China) was homogenized with various amounts of nonstoichiometric TiC_{0.78} (average particle size 5 µm, Zhuzhou cemented carbide plant, China) by milling the powders together for 10 h. Cylindrical samples were prepared by hot pressing at 1900°C and 35 MPa for 30 min under argon. The pure boron carbide sample was hot pressed at the same temperature for the same time, but at a higher pressure (39 MPa) to get a lower porosity. The electrical and thermal conductivities and Seebeck coefficient were measured up to 1200 K in vacuum. A two-probe method, using a chopped direct current, was employed to measure the electrical conductivity. Seebeck coefficients were determined from the linear relationship between the thermal electromotive force and temperature difference between the two ends of the sample. Thermal conductivity was measured by using the common laser flash method. The apparent porosity of the samples was determined by the method given by the American Society of Testing and Materials Criterion (ASTMC375)[12].

3. Results and discussion

From the XRD results, it can be seen that the TiC_{0.78} is completely converted into TiB₂. It also shows that the TiB₂ content increases with the amount of TiC_{0.78} added and that there is very little carbon content compared to the amounts of B₄C and TiB₂. The apparent porosity of the samples containing 0, 12.5, and 25.4 vol% TiB₂ is 13.0, 14.0 and 0.82%, respectively. This indicates that adding TiC_{0.78} can be an effective method of improving the densification of B₄C ceramics. From scanning electron microscopy



Fig. 4. Dimensionless ZT of the samples as a function of temperature.

observations, it can be seen that the average grain size of the TiB₂ and B₄C is nearly the same (about 1 μ m).

Fig. 1 shows that the electrical conductivity of the samples increases rapidly with the content of TiB₂. Note that the electrical conductivity for the 12.5 vol% TiB₂/B₄C sample increases with temperature as does the undoped semiconducting B₄C sample. However, the electrical conductivity for the 25.4 vol% TiB₂/B₄C decreases with temperature, indicating metallic behavior.

The 12.5 vol% TiB₂/B₄C sample is a p-type semiconductor like the undoped B₄C, since both Seebeck coefficients remain positive and increase with temperature as shown in Fig. 2. The Seebeck coefficient of the 12.5 vol% TiB₂/B₄C is always lower than that of the undoped sample at the same temperature. However, the 25.4 vol% TiB₂/B₄C sample behaves like an n-type material with a negative Seebeck coefficient, whose absolute value increases slowly with temperature.

The thermal conductivity of the samples as a function of temperature is shown in Fig. 3. The thermal conductivity increases monotonically with the amount of TiB₂, because of the high thermal conductivity of TiB₂ compared with B₄C. The thermal conductivity for the undoped B₄C and 12.5 vol% TiB₂/B₄C samples both decreases with temperature, whereas the thermal conductivity of the 25.4 vol% TiB₂/B₄C sample increases with the temperature and is nearly constant above about 900 K.

Figs. 1–3 clearly show that the thermoelectric properties change rapidly as the amount of TiB₂ goes from 12.5 to 25.4 vol%, which suggests that conducting phase (TiB₂) in the samples becomes continuous in this range and that ϕ_c for TiB₂ is in the range of 0.125–0.254. The transport properties of the 12.5 vol% TiB₂/B₄C sample are similar to the B₄C, with the dominant charge carrier being a small polaron (B₁₁C)⁺ [9], because the TiB₂ particles and clusters are isolated in a B₄C matrix. For the 25.4 vol% TiB₂/B₄C sample, the conducting phase (TiB₂) has a continuous or percolation path [7,8] through the whole sample and thus dominates the thermoelectric properties of the composite. Therefore, although the electrical conductivity of B_4C increases with temperature [9], the electrical conductivity of TiB₂ decreases with temperature [13] and the electrical conductivity for the 25.4 vol% TiB₂/B₄C sample decreases with temperature.

The Seebeck coefficient measurement also shows such changes with TiB₂ content (Fig. 2). The Seebeck coefficient changes from positive to negative value as the content of TiB_2 increases from 12.5 to 25.4 vol%. That is, when the distribution of TiB2 particles in the composite changes from a dispersed to a continuous state, the dominant conducting mechanism in the composites changes from small polaron hopping to electronic transport. There is also the intriguing possibility that, with a p-type conductor as the second phase, one could obtain p-type B₄C-based composites. Also because B_4C (or B_rC) is a well-known p-type thermoelectric material, the search for n-type B_4C (or B_xC)-based materials has attracted much attention [14,15], but until now it has been unsuccessful. The present work indicates that n-type B_4C (or B_xC)-based materials may be obtained by combining a metallic-conducting phase (electronic conductor) with B_4C (or B_xC) in a composite.

The dimensionless ZTs calculated from the measurements of the electrical conductivity, thermal conductivity and Seebeck coefficient for all the samples are given as a function of temperature in Fig. 4, which shows that the values of ZT for the 12.5 vol% TiB2/B4C sample are lower than that of the undoped B₄C sample at all temperatures, as predicted by EMT [6]. However, for the 25.4 vol% TiB_2/B_4C sample, the values of ZT are higher than that of the undoped sample below about 700 K, contradicting the EMT prediction [6] and showing that this prediction does not hold necessarily for the percolation system. Note that all the samples have different porosities and that the electrical conductivity, as well as the thermal conductivity of the samples, decreases with porosity, while the Seebeck coefficient of the sample is not very sensitive to porosity [16]. Therefore, the porosity of the present samples probably has no pronounced effect on their ZT values.

4. Conclusion

The amount of the second conducting phase (TiB₂) affects the thermoelectric properties of TiB₂/B₄C composite ceramics. For the 12.5 vol% TiB₂/B₄C sample, the value of ZT is always lower than that of the undoped B₄C sample, while for 25.4 vol% TiB₂/B₄C sample, the value of ZT is higher than that of the undoped B₄C sample at temperatures below 700 K. This implies that it is possible to get an improvement in ZT using a continuum percolating composite with an optimized microstructure. Further experiments should be made on composites with volume fractions of TiB₂ closer to the percolation threshold, as well as on other similar systems such as W_2B_5/B_4C , or even systems with other semiconducting and conducting phases.

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